

N-Channel Reduced Q_g , Fast Switching MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
30	0.007 at $V_{GS} = 10$ V	16	11
	0.0095 at $V_{GS} = 4.5$ V	13.5	

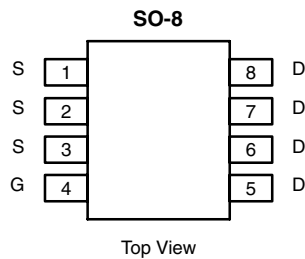
FEATURES

- TrenchFET[®] Gen II Power MOSFETS
- PWM Optimized
- 100 % R_g Tested

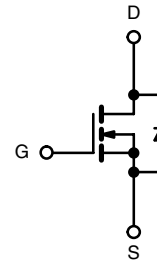


APPLICATIONS

- DC/DC Conversion for PC



Ordering Information: Si4386DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C unless otherwise noted					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	30		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	16	11	A
		$T_A = 70$ °C	13	9	
Pulsed Drain Current	I_{DM}	± 50			
Continuous Source Current (Diode Conduction) ^a	I_S	2.8	1.3		
Single Pulse Avalanche Current	I_{AS}	20		mJ	
Avalanche Energy	E_{AS}	20			
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	3.1	1.47	W
		$T_A = 70$ °C	2	0.95	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient (MOSFET) ^a	R_{thJA}	$t \leq 10$ sec	34	40	°C/W
		Steady State	71	85	
Maximum Junction-to-Foot (Drain)	R_{thJF}	18	22		

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.



MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.5	2.0	2.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 16\text{ A}$		0.0058	0.007	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 13.5\text{ A}$		0.0078	0.0095	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 16\text{ A}$		51		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.8\text{ A}, V_{GS} = 0\text{ V}$		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 16\text{ A}$		11	18	nC
Gate-Source Charge	Q_{gs}			5.8		
Gate-Drain Charge	Q_{gd}			3.0		
Gate Resistance	R_g		0.8	1.7	2.5	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		12	18	ns
Rise Time	t_r			9	14	
Turn-Off Delay Time	$t_{d(off)}$			35	53	
Fall Time	t_f			10	15	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		25	50	

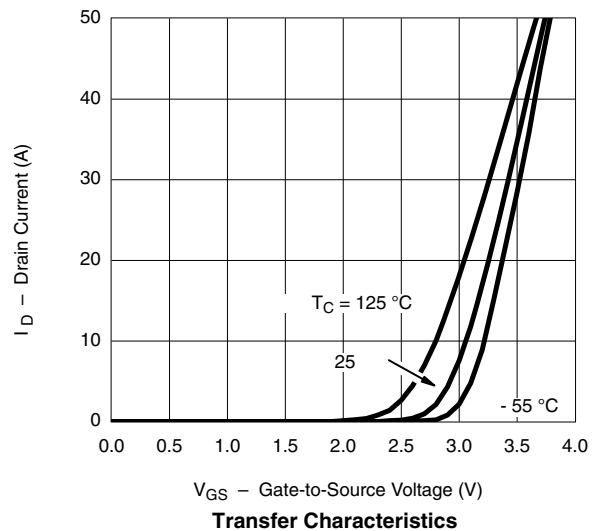
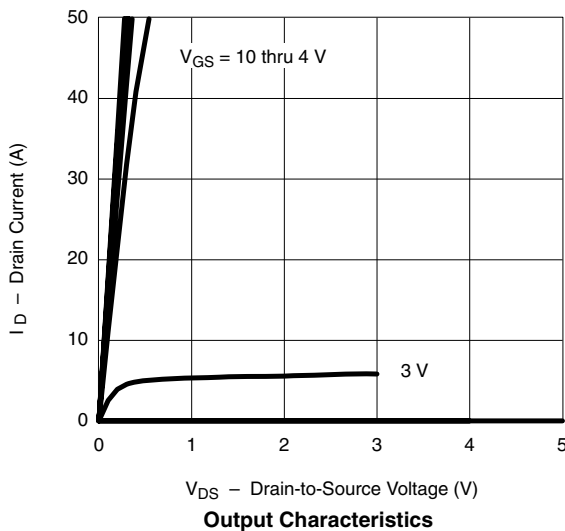
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

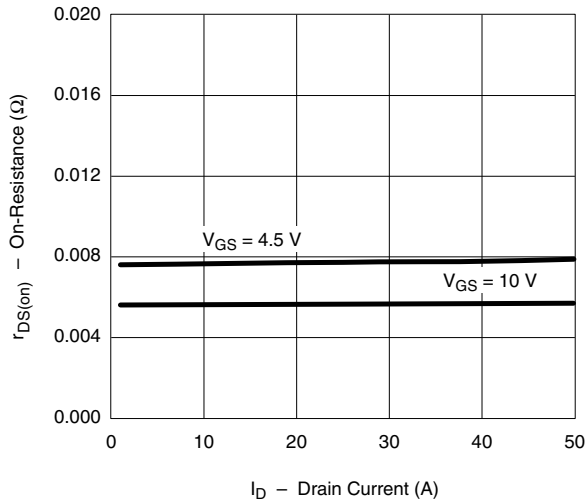
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

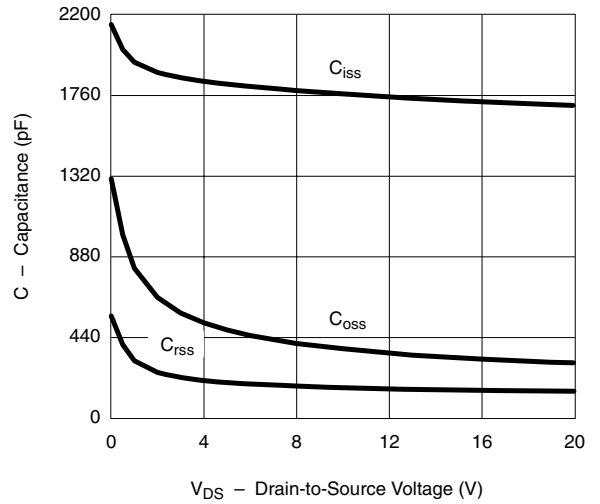
TYPICAL CHARACTERISTICS 25 °C unless noted



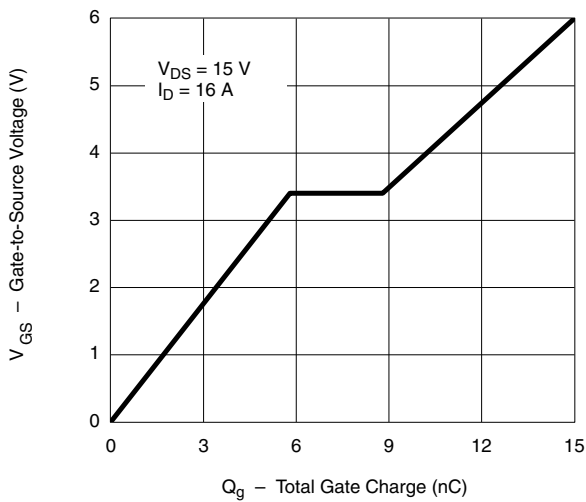
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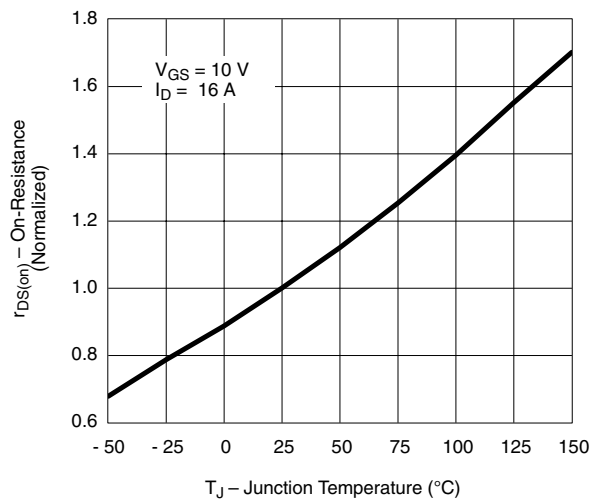
On-Resistance vs. Drain Current



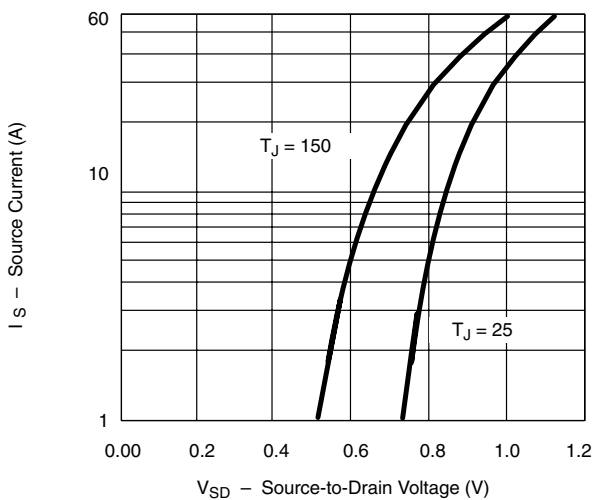
Capacitance



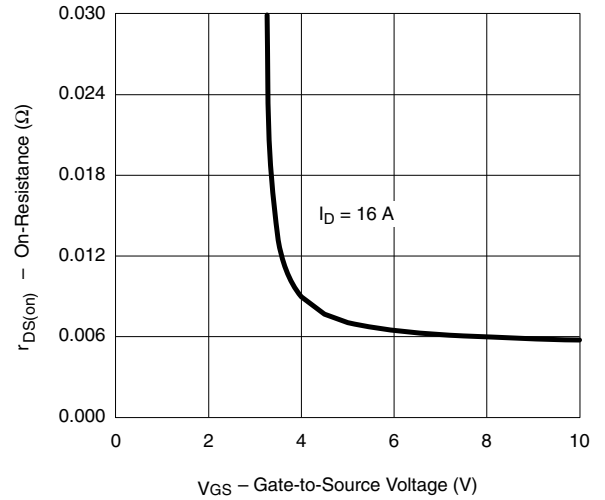
Gate Charge



On-Resistance vs. Junction Temperature

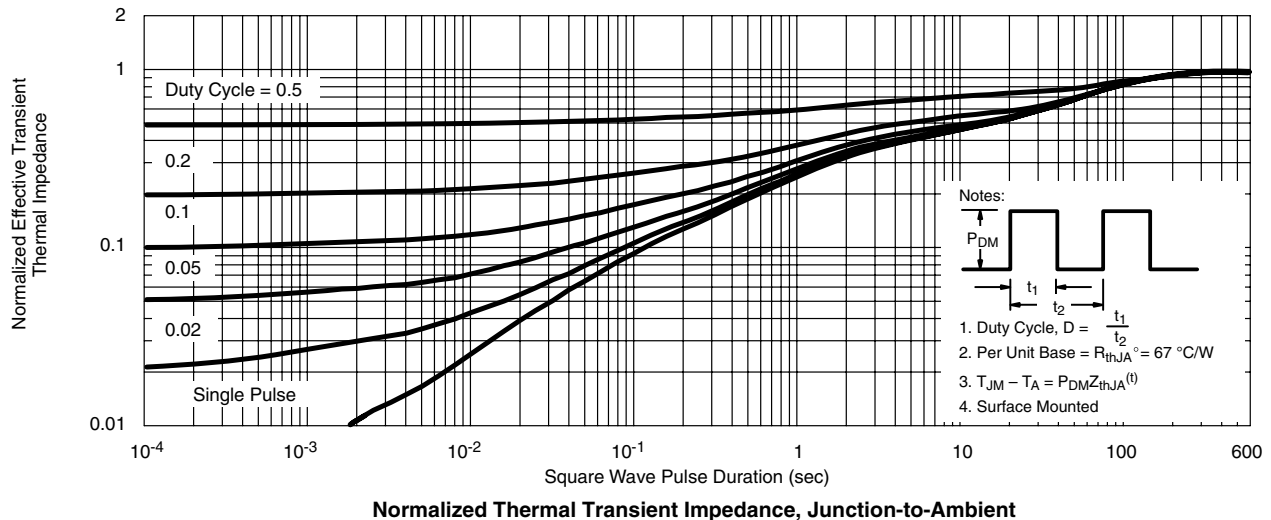
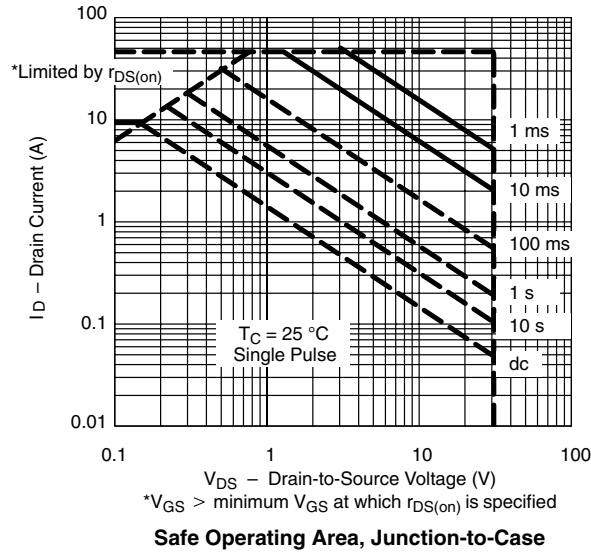
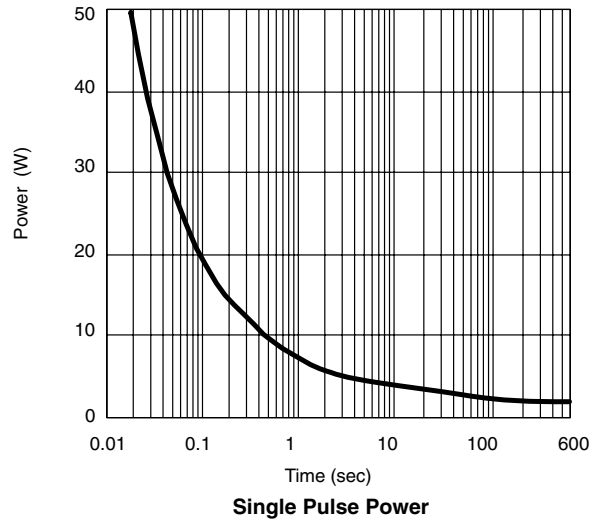
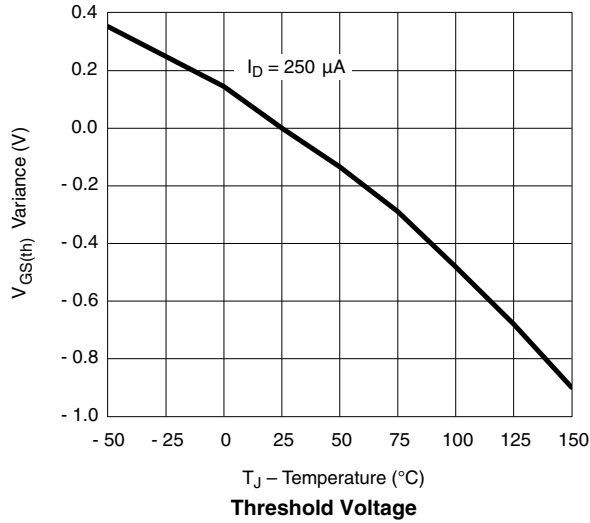


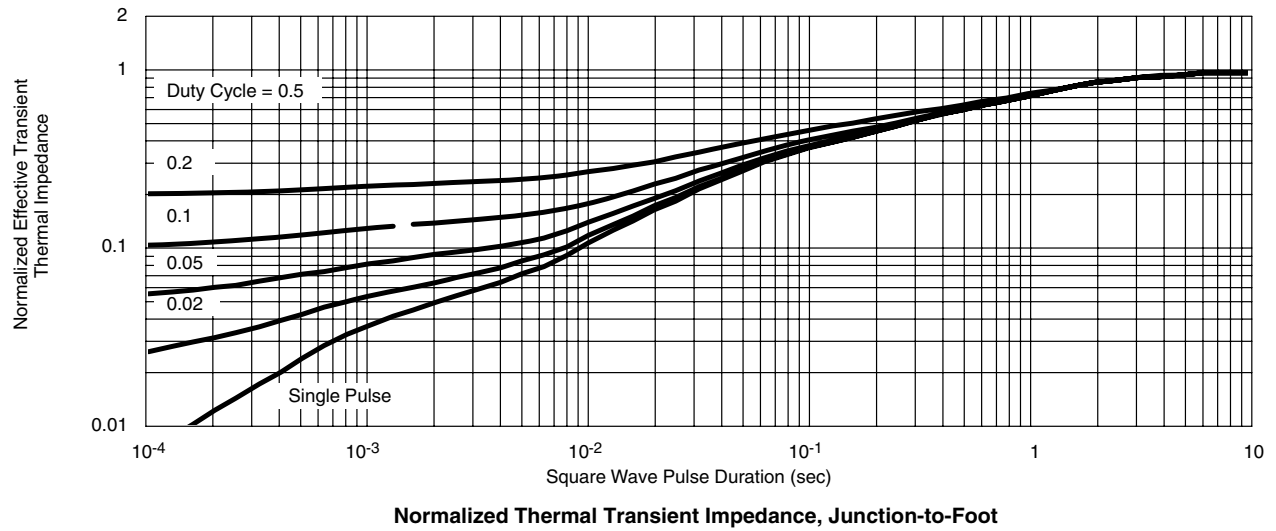
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless noted





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